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13 2004 E UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Hiroshi KUDO et al.

Group Art Unit: 2822

Serial No.: 10/754,577

Examiner: ZARABIAN, AMIR

Filed: January 12, 2004

Confirmation No.: 8244

For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING

THE SAME

Attorney Docket No.: 042012 Customer Number: 38834

INFORMATION DISCLOSURE STATEMENT PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

July 13, 2004

Sir:

Applicants direct the attention of the Patent and Trademark Office to the document listed on the attached Form PTO-1449. A copy of each listed document is attached.

No fee or certification is required in connection with this Information Disclosure Statement, because it is being submitted prior to the issuance of a first official action on the merits or expiration of the three month period following the filing date or the entry of the national stage of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can, in the first instance, determine any materiality thereof to the claimed invention. Applicant respectfully requests that the information be expressly considered during the prosecution of this application and that the documents cited in the attached Form PTO-1449 be made of record therein and appear on the first page of any patent to issue therefrom.

Information Disclosure Statement Attorney Docket No. 042012 Serial No. 10/754,577

The Commissioner is authorized to charge our Deposit Account No. 50-2866 for any fee that is required to effect consideration of this statement.

Respectfully submitted,

WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP

Ken-Ich Hattori Attorney for Applicants Registration No. 32,861

KH/ak Westerman, Hattori, Daniels & Adrian, LLP 1250 Connecticut Avenue, NW Suite 700 Washington, D.C. 20036

Tel.: (202) 822-1100 Fax.: (202) 822-1111

Enclosures: PTO-1449, 7 references

INFORMATION DISCLOSURE OF STATION Atty. Docket No. 042012

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TATION Applican

Applicant(s): Hiroshi KUDO et al.

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U.S. PATENT DOCUMENTS

JUL 1 3 2004			U.B. I ATENT I			Filing Date	
Examiner &		Document No.	Name	Date	Class	Subclass	(If appropriate)
Initial	AA						
	AB						
	AC						
	AD						
	AE_						

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document No.		Date	Country	Translation (Yes or No)	
	AF	11-251595	09/17/1999	Japan	Yes (Abstract Only), see page 2 in the spec.	
	AG	11-261063	09/24/1999	Japan	Yes (Abstract Only), see page 2 in the spec.	
	AH	2001-024187	01/26/2001	Japan	Yes (Abstract Only), see page 2 in the spec.	
	AI	2001-274379	10/05/2001	Japan	Yes (Abstract Only), see pages 2 and 52 in the spec.	
	AJ	10-125677	05/15/1998	Japan	Yes (Abstract Only)	

OTHER DOCUMENTS

	AK	Murarka, S. P., "Silicides for VLSI Applications", Academic Press, Inc., pp. 88~95, 1983, (see pages 3 and 44 in the spec.)				
	AL	Qin M. et al., "Investigation of Polycrystalline Nickel Silicide films as a Gate Material", Journal of The Electrochemical Society, 148 (5) (The Electrochemical Society, Inc.), pp. G271~G274 (2001) (see pages 3 and 49 in the spec.)				
Examiner		Date Considered				